New results on the annealing behaviour of the E4/E5-defect

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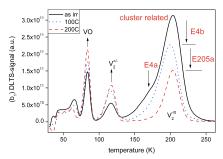
17th RD50 meeting 2010, CERN 17-18.11.2010



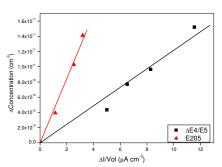
What is the origin of high leakage current?

Crystal defects in the silicon bulk create leakage current

⇒ Combine microscopic and macroscopic measurements



DLTS measurements show defect concentrations...

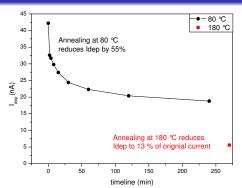


... revealing the correlation of defects and LC



Impact of E4/E5 and E205a

- 55 % of the total LC anneals out during 80 °C annealing
- After annealing at 180 ℃ only 10 % of the LC is left



Annealing of crystal defects

- The E4/E5 defect anneals at 80 ℃
- E205a anneals between 140 ℃ to 200 ℃



$\overline{E4/E5}$ is one bistable configuration of V_3

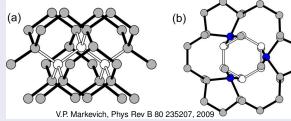
Three silicon vacancies in two configurations

Planar configuration

2 acceptor levels E4 & E5

Four-fold configuration (ffc)

• 1 acceptor level E75



Change of configuration (recovery) possible by

- annealing at 80 °C ⇒ produces E75
- injection of high current ⇒ produces E4/E5



Materials & measuring techniques

Materials

MCz & FZ Neutron irradiated $\Phi_{eq} = 1 - 6 \times 10^{11}$



Capacitance/current-voltage characteristics (CV-IV)

Measurement of diode characteristics stabilised at 20 °C

⇒ Endcapacitance, depletion voltage and leakage current

Deep level transient spectroscopy (DLTS)

Measurement of capacitance transients due to emission of charge carriers

⇒ Defect concentrations

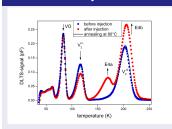


Can we make use of E4/E5 bistability

Bistability used to find origin of LC

If defect switched on/off LC should follow

DLTS after injection



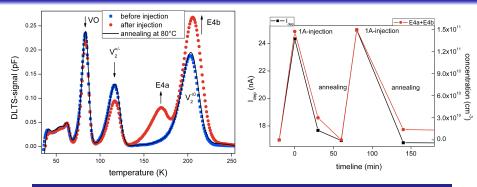
Annealing procedure

- Isochronal annealing step
- ② Injection of current at 0 °C
- Isothermal annealing

Measurements: CV/IV, DLTS/TSC, charge capture



Correlation of LC and E4/E5

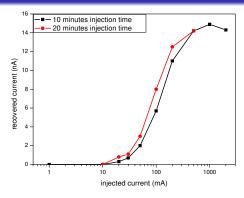


Direct correlation found

- Which mechanism leads to change of configuration?
- How much current do we need to inject?



Variation of the injected current



10 minutes injection:

- Saturation reached at 1 A
- Annealing effects very high at 2 A (≈15 W at 0 °C)

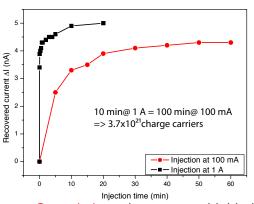
20 minutes injection:

No change of saturation value

I (A)	charge density $(s^{-1}cm^{-3})$	accumulated charge (cm $^{-3}$)
1	4.5×10^{17}	3.7×10^{21}
0.5	1.8×10^{16}	1.9×10^{21}



Variation of injection time



- LC not fully recovered even after 100 minutes at 100 mA
- Charge carrier density leads to change of configuration
- Charge need to overcome potentials in cluster defects

Speculation: cluster core shielded by potentials

⇒ High charge densities needed





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- Semi circles are charge trapping positions





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- With high injection also the shielded core can be reached



Summary & Outlook

Summary

- Correlation of E4/E5 with LC nicely seen
- Bistability used to recover LC
- Charge density important for recovery of LC

Outlook - Electrons or holes responsible?

- Red laser from front ⇒ electron injection
- Red laser from rear ⇒ hole injection
- Diode window allows 12 % of LC recovery

